



650 V power Schottky silicon carbide rectifier





Features

- No or negligible reverse recovery
- · Temperature independent switching behavior
- · High forward surge capability
- Operating T_i from -40 °C to 175 °C
- · Power efficient product
- ECOPACK[®]2 compliant

Applications

- DC/DC converter
- · High frequency inverter
- · Boost PFC function

Description

The STPSC16H065A SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode, packaged in TO-247, will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

Product status link

STPSC16H065A

Product summary			
I _{F(AV)}	16 A		
V_{RRM}	650 V		
T _j (max.)	175 °C		
V _F (typ.)	1.56 V		

Product label





1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter			Unit
V_{RRM}	Repetitive peak reverse voltage $T_j = -40 ^{\circ}\text{C}$ to +175 $^{\circ}\text{C}$		650	V
I _{F(RMS)}	Forward rms current		22	Α
I _{F(AV)}	Average forward current	T _c = 115 °C ⁽¹⁾ , DC current	16	Α
		t_p = 10 ms sinusoidal, T_c = 25 °C	120	
I_{FSM}	I _{FSM} Surge non repetitive forward current	t _p = 10 ms sinusoidal, T _c = 125 °C	105	Α
		t _p = 10 μs square, T _C = 25 °C	800	
I _{FRM}	Repetitive peak forward current	$T_c = 115 ^{\circ}C^{(1)}, T_j = 175 ^{\circ}C, \delta = 0.1$	66	Α
T _{stg}	Storage temperature range	-55 to +175	°C	
Tj	Operating junction temperature			°C

^{1.} Value based on $R_{th(j-c)}$ max.

Table 2. Thermal resistance parameters

Symbol	Parameter –	Va	Unit	
Symbol		Тур.	Max.	Oilit
R _{th(j-c)}	Junction to case	0.95	1.5	°C/W

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
L (1) Deverse leeken	Povorno logicado gurrant	T _j = 25 °C	$V_R = V_{RRM}$	-	12	140	μA
IR'	I _R ⁽¹⁾ Reverse leakage current	T _j = 150 °C		-	120	560	
V _F ⁽²⁾ Forward voltage drop	Forward voltage drap	T _j = 25 °C	I _F = 16 A	-	1.56	1.75	V
	Forward voitage drop	T _j = 150 °C		-	1.98	2.50	

- 1. Pulse test: $t_p = 10 \text{ ms}, \ \delta < 2\%$
- 2. Pulse test: $t_p = 500 \,\mu\text{s}, \, \delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.07 \times I_{F}^{2}_{(RMS)}$$

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

DS12768 - Rev 1 page 2/9



Table 4. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Тур.	Unit
Q _{Cj} ⁽¹⁾	Total capacitive charge	V _R = 400 V	41	nC
C.	C Tatal associtores	V _R = 0 V, T _c = 25 °C, F = 1 MHz	750	
C _j Total capacitance	V _R = 300 V, T _c = 25 °C, F = 1 MHz	76	pF	

1. Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int\limits_0^{V_R} C_j(V) dV$

1.1 Characteristics (curves)

Figure 1. Forward voltage drop versus forward current (typical values, low level)

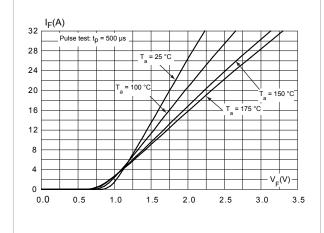


Figure 2. Forward voltage drop versus forward current (typical values, high level)

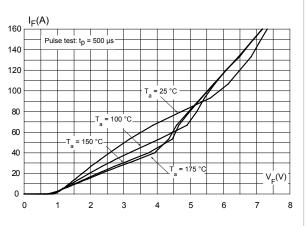


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

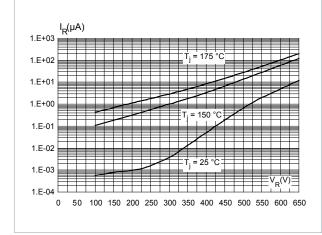
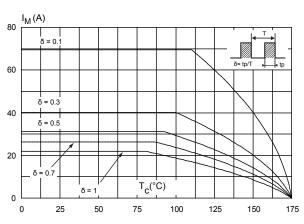


Figure 4. Peak forward current versus case temperature



DS12768 - Rev 1 page 3/9



200

0

0.1

1.0

Cj(pF)

800

F = 1 MHz

V_{OSC} = 30 mV_{RMS}

T_j = 25 °C

Figure 5. Junction capacitance versus reverse

voltage applied (typical values)

junction to case versus pulse duration 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 Single pulse 0.1 $t_p(s)$ 0.0 1.E-05 1.E-04 1.E-03 1.E-02 1.E-01 1.E+00

Figure 6. Relative variation of thermal impedance

Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

10.0

100.0

1000.0

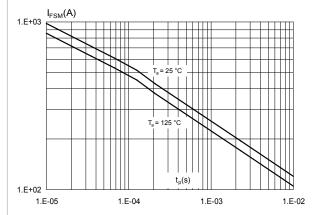
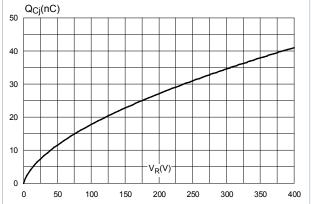


Figure 8. Total capacitive charges versus reverse voltage applied (typical values)



DS12768 - Rev 1 page 4/9



Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-247 package information

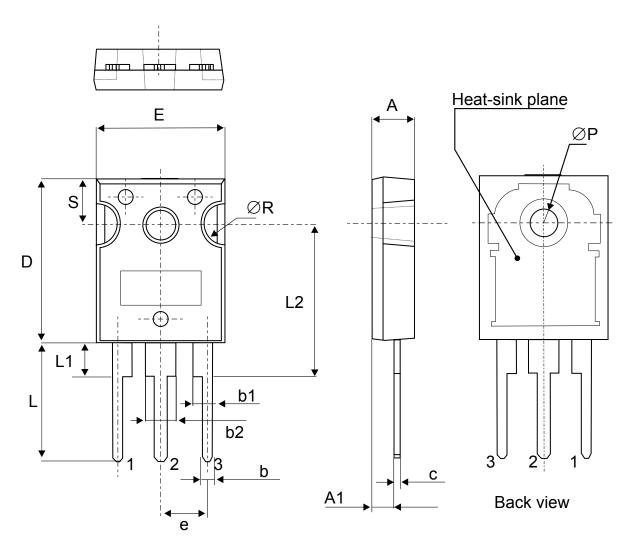
Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 N·m

Maximum torque value: 1.0 N·m

Figure 9. TO-247 package outline



DS12768 - Rev 1 page 5/9



Table 5. TO-247 package mechanical data

			Dimer	nsions		
Ref.		Millimeters		Inc	hes (for reference o	only)
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
С	0.40		0.80	0.015		0.031
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
е	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
ØP	3.55		3.65	0.139		0.143
ØR	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

DS12768 - Rev 1 page 6/9



3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC16H065AW	STPSC16H065AW	TO-247	4.43 g	30	Tube

DS12768 - Rev 1 page 7/9



Revision history

Table 7. Document revision history

Date	Version	Changes
08-Oct-2018	1	Initial release.

DS12768 - Rev 1 page 8/9



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DS12768 - Rev 1 page 9/9

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